CSE 321b

Computer Organization (2)

تنظيم الحاسب (2)



3rd year, Computer Engineering
Winter 2016
Lecture #2



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Credits to Dr. Ahmed Abdul-Monem Ahmed for the slides

Adminstrivia

- Schedule:
 - —Lectures: Monday 9:00am 11:30am
 - —Tutorials: Sunday 10:00am 11:30am
 - —Office hour: TBA
- Assignment #1:
 - —To be released next week

Website: http://www.bit.do/hshehata-courses-zu-cse321b

Office hours: TBA

Ch 5: Internal Memory (Cont.)

Error Correction

- Semiconductor memory is subject to errors
 - Rate: 1 error/hour to 1 error/century in a 1GB memory!
 - Types: hard and soft.

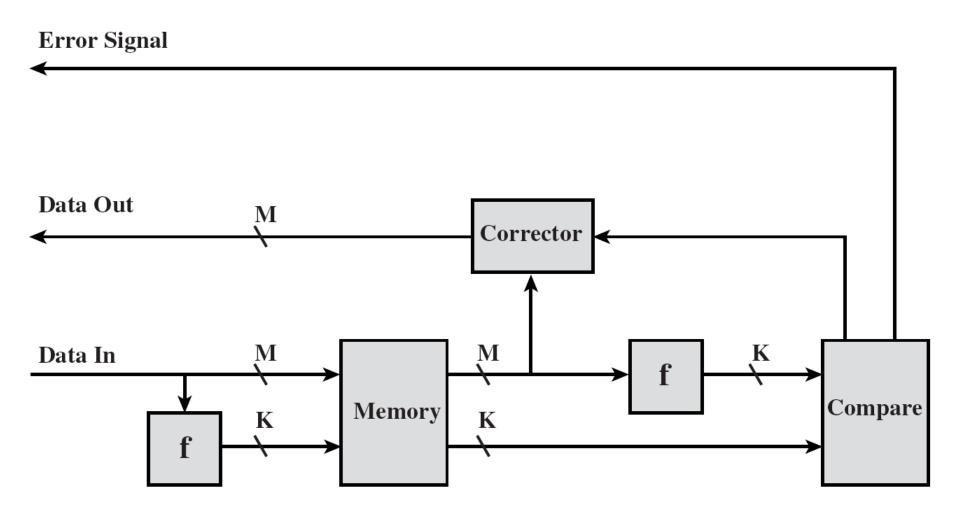
Hard Failure

- Permanent physical defect.
- Mem. cells can't store data: stuck at 0 or 1, or switching.
- Caused by harsh environments, manufacturing defects, or wear.

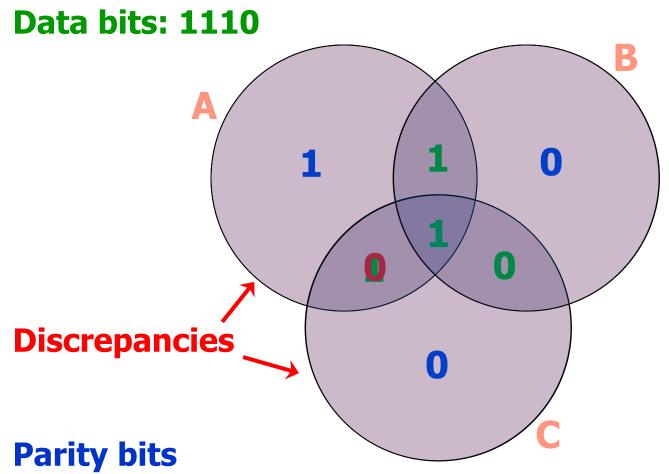
Soft Error

- Random, non-destructive event that alters contents of one or more memory cells.
- No permanent damage to memory.
- Caused by power supply problems or alpha particles.
- Detected/corrected using Hamming error correcting code.

Error-Correcting Code Function



Hamming Error-Correcting Code



Chosen so that total number of 1s in each circle is even.

By checking the parity bits, discrepancies are found -> error can be easily found and corrected.

Error-Correcting Codes

- A codeword consists of N bits split into M data bits and K check (redundant) bits
 - -N=M+K
- Hamming distance: Number of bit-positions in which two codewords differ.
 - Ex.: 11001001, 10100001 → Hamming distance = 3 → 3 bit errors are needed to convert one into the other.
- Note: in a code, not all 2^N codewords are legal.
- Hamming distance of the whole code: minimum Hamming distance between 2 legal codewords.
- A distance d code can:
 - **Detect:** d-1 errors.
 - **Correct:** (d-1)/2 errors if d is odd, or (d/2)-1 errors if d is even.

Error Detection/Correction

- Detection: parity bit.
 - Distance = 2 → can detect up to 1 bit error.
 - Ex.: data=1011010 → codeword=10110100 → any codeword with a distance = 1 (such as: 10100100) is considered illegal → single-bit errors are detectable.
- Correction: Consider a code with 4 valid codewords:

- Distance = $5 \rightarrow$ can correct up to 2 bit errors.
- If 0000000111 arrives, → 0000011111
- If 000000000 becomes 000000111 due to 3 errors → cannot be corrected properly.

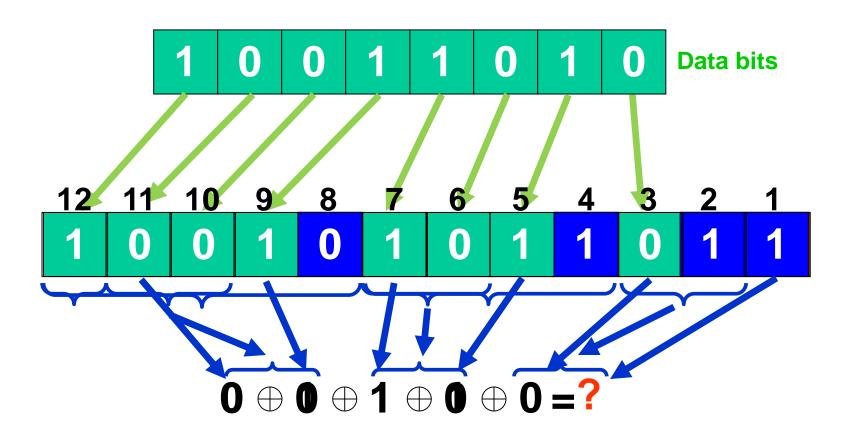
Single Bit Error Correction

Design a code to correct all single bit errors.

- M = data bits, K = check bits
- N = M + K
- Rule: Choose Ks.t. $M + K + 1 \le 2^K$
- Justification:
 - Each of the 2^M legal words has N illegal codewords at distance 1.
 - Thus, each of the 2^M legal words requires (N + 1) bit patterns dedicated to it.
 - $(N+1) 2^M \le 2^N \to M+K+1 \le 2^K$

Hamming Code

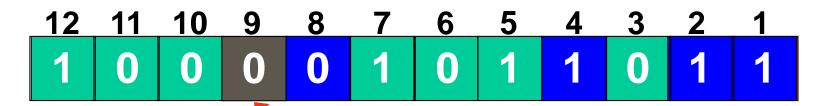
$$2^{K}-1 \ge M+K \implies 2^{K} \ge 9+K \implies K=4$$



Bit position **2**

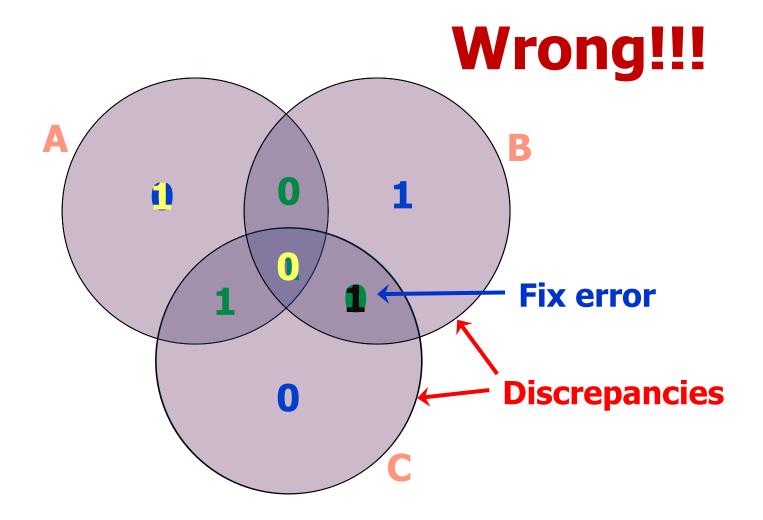
Bit position 8: 0

Hamming Code (2)

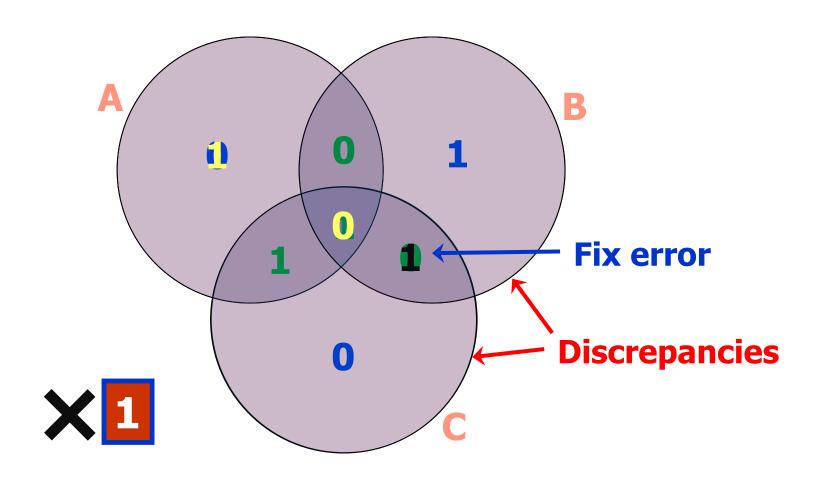


- Assume error in bit 9.
- Recompute the check bits.
- Bit 1 = 0 (error).
- Bit 2 = 1.
- Bit 4 = 1.
- Bit 8 = 1 (error).
- Error is in bit position $=1+8=9 \rightarrow$ flip it (correction).

Hamming SEC-DED Code



Hamming SEC-DED Code (2)



Increase in Word Length with Error Correction

	Single-Error Correction		Single-Error Correction/ Double-Error Detection	
Data Bits	Check Bits	% Increase	Check Bits	% Increase
8	4	50	5	62.5
16	5	31.25	6	37.5
32	6	18.75	7	21.875
64	7	10.94	8	12.5
128	8	6.25	9	7.03
256	9	3.52	10	3.91

Advanced DRAM Organization

- Interface to MM is a system bottleneck.
- DRAM chip is the main building block of MM.
- Basic DRAM architecture same since 1970s!
- Enhancements to basic DRAM architecture
 - —Synchronous DRAM (SDRAM)
 - DDR-SDRAM, DDR2-SDRAM, DDR3-SDRAM
 - —Rambus DRAM (RDRAM)
 - —Cache DRAM (CDRAM)

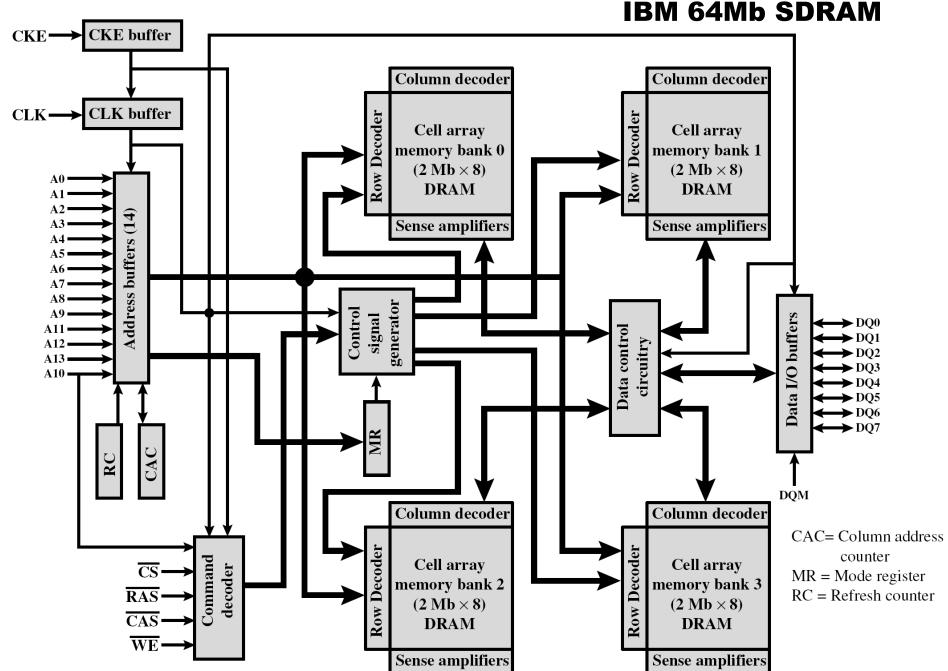
Synchronous DRAM (SDRAM)



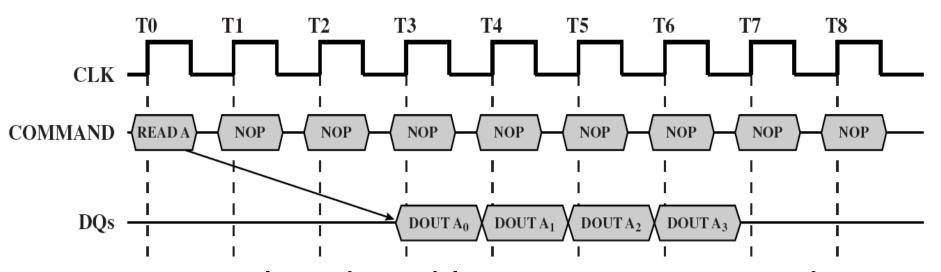
- Unlike traditional DRAM (which is asynchronous), SDRAM exchanges data with CPU synchronized to an external clock (system bus).
- No wait states!
 - —SDRAM moves data in/out under control of system clock.
 - —CPU issues command and address.
 - —Latched by the SDRAM.
 - —SDRAM responds after a number of clock cycles.
 - —Meanwhile, CPU can do other tasks → no waits.

Synchronous DRAM (SDRAM) (2)

- Burst mode: a series of data bits can be clocked out rapidly after the first bit has been accessed.
- Eliminates row and column address setup time.
- Useful when the required bits are in sequence and in the same row of the array as the initial access.
- Multiple-bank internal architecture improves opportunities for parallelism.
- Mode Register (MR)
 - —Specifies burst length.
 - —Allows programmer to adjust latency between read request and data transfer.



SDRAM Operation



- Burst type, length and latency are set in mode reg.
 - —Type: interleaved or sequential
 - —In the example: length=4 and latency=3
- Burst read command is initiated.
 - —At the rising edge of the clock: CS & CAS → low, and RAS & WE → high.
- Address inputs determine starting column for burst.

Enhanced versions of SDRAM

- Double Data Rate (DDR-SDRAM)
 - —produces two words of data every memory cycle
 - —sends data to CPU twice per clock cycle (at leading & trailing edges of the clock)
 - -2x data rate of SDRAM (with same cell speed)

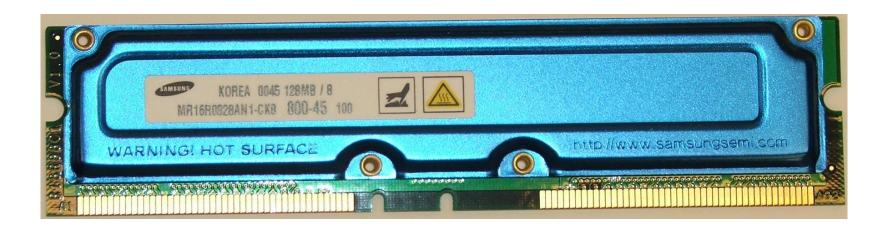
DDR2-SDRAM

- —produces four words of data every memory cycle
- -2x bus speed & data rate of DDR (with same cell speed)

DDR3-SDRAM

- —produces eight words of data every memory cycle
- -2x bus speed & data rate of DDR2 (with same cell speed)

Rambus DRAM (RDRAM) (1)

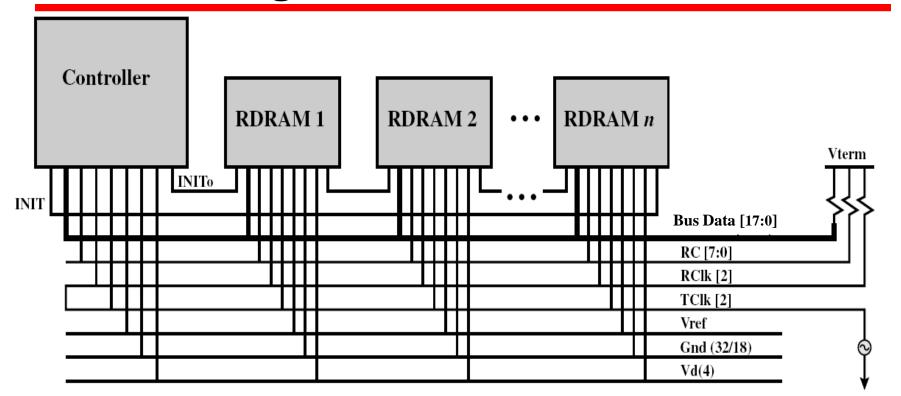


- Adopted by Intel for Pentium & Itanium in late 90s.
- Was main competitor to SDRAM.
- Chips are vertical packages all pins on one side.
- Data exchange over 28 wires < 12 cm long.
- Bus can address up to 32 RDRAM chips and is rated at 1.6 GBps.

Rambus DRAM (RDRAM) (2)

- Asynchronous block-oriented protocol
 - Initial 480 ns access time.
 - Then 1.6 GB/s.
- What makes this speed possible is the bus itself, which defines impedances, clocking, and signals very precisely.
- RDRAM gets a memory request over the highspeed bus (unlike conventional DRAMs controlled by RAS, CAS, R/W, and CE).
- This request contains address, operation, number of bytes.

RDRAM Diagram



- Controller and a number of RDRAM modules connected via a common bus.
- Bus: 18 data lines, cycling at twice the clock rate → 800 Mbps per line.
- Address and control signals: 8 lines (RC)
- Clock starts at the far end from the controller, propagates to the controller end, then loops back.
- Module sends data to the controller synchronously to the clock to master.
- Controller sends data to a module synchronously with the clock in the opposite direction.

Cache DRAM (CDRAM)

- CDRAM integrates a small SRAM cache (16 kb) onto a generic DRAM chip.
- CDRAM can be used in two ways:
 - 1. As a **true cache** with 64-bit lines.
 - 2. As a **buffer** to support serial access of a data block.
 - -e. g., to refresh a bit-mapped screen, the CDRAM can prefetch the data from the DRAM into the SRAM buffer. Subsequent accesses to the chip results in accesses to the SRAM only.

Reading Material

- Stallings, Chapter 5:
 - —Pages 170 180